

forming a first insulating layer comprising silicon, carbon and nitrogen on said first insulating layer;

selectively etching said second insulating layer until the surface of said first insulating layer is partially exposed,

selectively etching said first insulating layer with plasma, using said selectively-etched second insulating layer as a mask pattern; and

forming a new wiring layer on said second insulating layer after selectively etching said first insulating layer.

**IN THE DRAWINGS:**

Subject to the approval of the Examiner, please amend the drawings as shown in the accompanying Request for Approval of Drawing Change.

**REMARKS**

Claims 4-9 are now pending in this application.

In response to a telephonic restriction requirement by the Examiner on July 31, 2001, Applicant made an oral election of claims 4-9. Applicant affirms this oral election without traverse and has accordingly cancelled claims 1-3 without prejudice or disclaimer to the subject matter thereof.

In the Office Action dated August 15, 2001, the Examiner rejected claims 4-9 under 35 U.S.C. § 112, 2<sup>nd</sup> paragraph, as being indefinite. Applicant has obviated this rejection by amending claim 4 as suggested by the Examiner.

The Examiner also rejected claims 4-8 under 35 U.S.C. § 103(a) as being unpatentable over Zhao et al. in view of Kato et al. Applicant disagrees with the

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